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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		APPLICANT Toshiro HAYAKAWA, Toshiaki FUKUNAGA and Mitsugu WADA	
		FILING DATE May 20, 1999	GROUP 2881

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>13</i>	4,567,060	01/28/86	HAYAKAWA et al	427	87	

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

<i>12</i>		S. O'Brien et al, High power wide aperture AlGaAs-based lasers at 870nm, January 22, 1998, Vol.34, No.2, page 184 - 186
<i>13</i>		T. Fukunaga et al, Highly Reliable Operation of High-Power In GaAsP/InGaP/AlGaAs 0.8 μ m Separate Confinement Heterostructure Lasers, September 15, 1995, Vol. 34, No.9B, p.L1175 -L117
<i>13</i>		J.K. Wade et al, 6.1 W continuous wave front-facet power from Al-free active-region (λ = 805 nm) diode lasers, January 5, 1998, Vol., 72, No.1, p.4 - 6
<i>13</i>		M.A. Emanuel et al, High-Power Laser Diodes at Various Wavelengths, 1997, Vol. 3001, p.2 - 6
<i>13</i>		Low-threshold room-temperature cw operation of (AlGaAs) _m (GaAs) _n superlattice quantum well lasers emitting at ~ 680nm, September 7, 1987, Vol.51, p.707 - 709

EXAMINER <i>JEFFER ZAHN</i>	DATE CONSIDERED <i>2/7/2001</i>
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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				Applicant: Toshiro HAYAKAWA, et al.			
				Filing Date: May 20, 1999		Group: 2874 2881	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date (if appropriate)
13.		4,728,628	3/1/88	Fiddymet et al.	437	225	
FOREIGN PATENT DOCUMENTS							
		Document	Date	Country	Class	Sub- class	Translation Yes/No
13.		7-74425	3/17/95	Japan	H01S	3/18	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
13		Milind R. Gokhale, et al.; "High-Power High-Efficiency 0.98-μm Wavelength InGaAs-(In)GaAs(P)-InGaP Broadened Waveguide Lasers Grown by Gas-Source Molecular Beam Epitaxy" vol. 33; No. 12; December 1997; pages 2266-2276					
13		Electronics Letters; vol. 28; No. 16; pages 1531-1532; July 1992					
EXAMINER: JEFFREY RATH				DATE CONSIDERED: 2/7/2001			
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